24 February 2004

Updated Search

09/782,216

21 100		1 upaarea sea un	,	01/+84,21
L Number	Hits	Search Text	DB	Time stamp
-	0	476526.apn.	USPAT;	2003/07/29
			US-PGPUB;	11:13
			EPO; JPO;	
			DERWENT	
_	1	6547937.pn.	USPAT;	2003/07/29
		•	US-PGPUB;	14:25
			EPO; JPO;	
			DERWENT	
_	152	204/\$.ccls. and (cleaning adj electrode)	USPAT;	2003/07/28
		4 (US-PGPUB;	16:24
			EPO; JPO;	
			DERWENT	
_	17	(204/\$.ccls. and (cleaning adj electrode)) and	USPAT;	2003/07/28
	• • •	(microelectronic or wafer or semiconductor)	US-PGPUB;	16:24
		(microelectronic or water or senticonductor)	EPO; JPO;	10.24
			DERWENT	
	12396	201/\$ and (and game anthoda)	E .	2002/07/20
-	12370	204/\$.ccls. and (anode same cathode)	USPAT; US-PGPUB;	2003/07/29 10:53
			EPO; JPO;	10:55
		70221/	DERWENT	2002/07/00
-	1	782216.apn.	USPAT;	2003/07/29
			US-PGPUB;	13:12
			EPO; JPO;	
			DERWENT	
-	59395	204/\$.ccls.	USPAT;	2003/07/29
			US-PGPUB;	13:12
			EPO; JPO;	
			DERWENT	
-	35240	205/\$.ccls.	USPAT;	2003/07/29
			US-PGPUB;	13:13
			EPO; JPO;	
			DERWENT	
-	83968	204/\$.ccls. 205/\$.ccls.	USPAT;	2003/07/29
			US-PGPUB;	13:13
			EPO; JPO;	
			DERWENT	
-	10782	(204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
		semiconductor or wafer)	US-PGPUB;	13:13
			EPO; JPO;	
			DERWENT	
-	1310	((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
,		semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13:14
		or another or additional) near (electrode or cathode	EPO; JPO;	
		or anode))	DERWENT	
-	574	((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
-	·	semiconductor or wafer)) and ((clean\$5 or strip\$5	US-PGPUB;	13:18
ľ		deposit) near2 (anode or cathode or electrode))	EPO; JPO;	-
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	
			JC1744 C141	

-	174	(((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
		semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13:18
		or another or additional) near (electrode or cathode	EPO; JPO;	
-		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(microelectronic or semiconductor or wafer)) and		
		((clean\$5 or strip\$5 deposit) near2 (anode or		
		cathode or electrode)))		
1	93	((((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
-	23		US-PGPUB;	13:18
		semiconductor or wafer)) and ((second or secondary		13.10
		or another or additional) near (electrode or cathode	EPO; JPO;	
		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(microelectronic or semiconductor or wafer)) and		
		((clean\$5 or strip\$5 deposit) near2 (anode or		
		cathode or electrode)))) and (etch\$5)		
-	462	205/640,646,648,652,686.ccls.	USPAT;	2003/07/29
			U5-PGPUB;	14:26
			EPO; JPO;	
			DERWENT	
_	98	205/640,646,648,652,686.ccls. and clean\$5	USPAT:	2003/07/29
		aco, o 10,0 10,0 10,00%,000.0013. and cleanyo	US-PGPUB;	15:10
			EPO; JPO;	13.10
1	1		DERWENT	
1		204/204		0000 (07 (00
- .	744	204/224m.ccls.	USPAT;	2003/07/29
			US-PGPUB;	15:10
			EPO; JPO;	
			DERWENT	
-	2427	204/275.1,237,242,280.ccls.	USPAT;	2003/07/30
		•	U5-PGPUB;	15:02
			EPO; JPO;	
			DERWENT	
_	3092	204/224m.ccls. 204/275.1,237,242,280.ccls.	USPAT;	2003/07/29
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	15:10
			EPO; JPO;	
			DERWENT	
_	167	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
_	10/	The state of the s		15:12
		((electrochem\$7 or electrol\$7 or (electro adj	U5-PGPUB;	13:12
		chem\$7)) near2 (etch\$5 or polish\$3))	EPO; JPO;	
		(004/004	DERWENT	
-	100	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		(electropolish\$5)	US-PGPUB;	15:12
			EPO; JPO;	
			DERWENT	
-	57	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2004/02/24
,		((electropolish\$5) with (electrode or anode or	US-PGPUB;	14:28
		cathode))	EPO; JPO;	
		···	DERWENT	
-	87	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		(((electrochem\$7 or electrol\$7 or (electro adj	US-PGPUB;	15:21
		chem\$7)) near2 (etch\$5 or polish\$3)) with	EPO; JPO;	
		(electrode or cathode or anode))	DERWENT	ĺ
	809	t i i i i i i i i i i i i i i i i i i i		2002/09/01
_	609	(204/\$.ccls. 205/\$.ccls.) and ((((builld or built) adj	USPAT;	2003/08/01
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	09:03
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing))	DERWENT	

	r	Land to the state of the state	1100:=	0000 107 107
-	179	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:25
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same (remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4))	LICOAT	0000 (07 (00
-	804	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:28
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with ((builld or built) adj up) or deposit\$5 or		
		collect\$3))		
-	133	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:29
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with (((builld or built) adj up) or deposit\$5		
	_	or collect\$3)))		0000 (07.10-
-	3	(("6500324") or ("6174425")).PN.	USPAT;	2003/07/30
			US-PGPUB;	09:33
			EPO; JPO;	
			DERWENT;	
		004/4	IBM_TDB	0000 (07 (0.5
-	8867	204/\$.ccls. and (microelectronic or semiconductor or	USPAT;	2003/07/30
		wafer)	US-PGPUB;	10:30
			EPO; JPO;	
			DERWENT;	
	22.4	(004/4-1	IBM_TDB	2002/07/22
-	2347	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	10:31
	**	(fluid or solution or electrolyte))	EPO; JPO;	
			DERWENT;	
	4054	(204/4-1	IBM_TDB	2002/07/20
-	1056	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	13:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
	65	or opening or inlet or outlet)) ((201/\$ cols and (microslecture); or comissanductor	IBM_TDB USPAT;	2003/07/20
-	63	((204/\$.ccls. and (microelectronic or semiconductor	USPAT; US-PGPUB;	2003/07/30 13:17
		or wafer)) and ((anode or cathode or electrode) with	EPO; JPO;	13.17
		(fluid or solution or electrolyte) with (conduit or path	DERWENT;	
		or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with anode)	IBM_TDB	
_	75	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
	'5	or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:14
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	*****
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (mesh with (anode	IBM_TDB	
		or porous))	1011_100	
_	160	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode with (mesh	IBM_TDB	
		or porous))		
L	·	L	J	I

	140	(1204/4 - 12 - 1/1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1	LICDAT.	2002/07/20
-	110	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode with rotat\$5)	IBM_TDB	
-	125	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:16
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))	IBW_TDB	
	60	(((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
-	80	or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:23
]	I	EPO; JPO;	14.23
		(fluid or solution or electrolyte) with (conduit or path		
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode near2	IBW_LDB	
		(rotat\$5 or mov\$7))) and (((204/\$.ccls. and		
		(microelectronic or semiconductor or wafer)) and		
		((anode or cathode or electrode) with (fluid or		
		solution or electrolyte) with (conduit or path or		
		pathway or port or passage or passageway or flow or		
		opening or inlet or outlet))) and (anode with (mesh or		
		porous)))	LICDAT.	2002/07/20
-	2	6197182.pn.	USPAT;	2003/07/30 14:35
			US-PGPUB;	14.50
			EPO; JPO; DERWENT;	
			IBM_TDB	
	1349	204/\$.ccls. and (solution with ((rins\$4 or clean\$5)	USPAT;	2003/07/30
	1547	and (electroplat\$5 or electroly\$6 or plating)))	US-PGPUB;	14:39
		and (electropiarys or electrolygo or plannig)))	EPO; JPO;	11.09
			DERWENT;	
			IBM_TDB	
_	765	(204/\$.ccls. and (solution with ((rins\$4 or clean\$5)	USPAT;	2003/07/30
	, 05	and (electroplat\$5 or electroly\$6 or plating)))) not	US-PGPUB;	14:40
		rinsed!	EPO; JPO;	- 11 10
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	
_	3	((("6103096") or ("5614076") or ("5531874") or	USPAT;	2003/07/30
		(("5486282") or ("5543032") or ("5536388") or	US-PGPUB;	14:43
		("5567300") or ("5284554")).PN.) and ((rins\$ or	EPO; JPO;	
		clean\$) with (plating or electroly\$5 or	DERWENT;	
		electroplat\$5))	IBM_TDB	
_	5	6103096.URPN.	USPAT	2003/07/30
		0.000,010,14.	5517(1	14:44
-	15	(("6103096") or ("5614076") or ("5531874") or	USPAT;	2003/07/30
	"	("5486282") or ("5543032") or ("5536388") or	US-PGPUB;	14:49
		("5567300") or ("5284554")).PN.	EPO; JPO;	- 11 12
		(0007000) (1 (000100))).114.	DERWENT;	
			IBM_TDB	
_	29	5567300.URPN.	USPAT	2003/07/30
	-/			14:47
L	J			

-	20	5543032.URPN.	USPAT	2003/07/30
			1100.7	14:48
-	6	5536388.URPN.	USPAT	2003/07/30 14:48
	15	5486282.URPN.	USPAT	2003/07/30
-	15	5400202.UKPIN.	USPAT	14:48
	19	5284554.URPN.	USPAT	2003/07/30
_	1	3204334.0KIN.	001711	14:48
_	62	5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
}		5486282.URPN. 5284554.URPN.	US-PGPUB;	14:49
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	0	(5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.) and (clean\$5 with	US-PGPUB;	14:50
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
	24	(FE(7300 LIDDY)	IBM_TDB	2002/07/20
-	26	(5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.) and (remov\$5 with	USPAT; US-PGPUB;	2003/07/30 14:55
		(electrode or cathode or anode))	EPO; JPO;	14.55
		(electrode of carnode of anode))	DERWENT;	
			IBM_TDB	
_	83968	204/\$.ccls. 205/\$.ccls.	USPAT;	2003/07/30
		,	US-PGPUB;	14:56
			EPO; JPO;	
			DERWENT;	
	İ	,	IBM_TDB	:
-	3	(204/\$.ccls. 205/\$.ccls.) and (electrochem\$7 near	USPAT;	2004/02/24
		(micromachin\$5 or machin\$5)) and (clean\$ near	US-PGPUB;	14:32
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
	295	204/275.1,237,242,280.ccls. and (titanium with	IBM_TDB USPAT;	2003/07/30
_	293	(platinum or platinized))	US-PGPUB;	15:05
		(plantial or plantinged))	EPO; JPO;	15.05
			DERWENT	
_	83	(204/275.1,237,242,280.ccls. and (titanium with	USPAT;	2003/07/30
		(platinum or platinized))) and (microelectronic or	US-PGPUB;	15:06
		semiconductor or wafer)	EPO; JPO;	
			DERWENT	
-	18	(("5312532") or ("5344491") or ("5421987") or	USPAT;	2003/07/31
		("5431421") or ("5516412") or ("5925226") or	US-PGPUB;	11:08
		("6001235") or ("6228231") or ("6251250")).PN.	EPO; JPO;	
			DERWENT;	
	8	ep-0343502-\$.did. ep-0726698-\$.did.	IBM_TDB USPAT;	2003/07/31 11:11
_		jp-62297494-\$.did. jp-62297495-\$-did.	US-PGPUB;	2003/07/31 11.11
		jp-1120827-\$.did. jp-5175158-\$.did.	EPO; JPO;	
		jp-6260468-\$.did. jp-7211724-\$.did.	DERWENT;	
		jp-7284738-\$.did. jp-10172974-\$.did.	IBM_TDB	
		jp-11092993-\$.did. jp-2000017480-\$.did.		

_	840	(204/\$.ccls. 205/\$.ccls.) and ((((build or built) adj	USPAT;	2003/08/01
	070	up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	09:04
		cathode or electrode) with (distance or gap or	EPO; JPO;	07.04
		spacing))	DERWENT	
	2	6328872.pn.	USPAT;	2004/02/24
-		1 032007 2.pn.	US-PGPUB;	13:32
]	~		13.32
	İ		EPO; JPO;	
		(#3305000# #343(050# #300074(# #305000#	DERWENT	0004/00/04
-	22	("3395092" "3436259" "3890746" "3959089"	USPAT	2004/02/24
		"4153523" "4395320" "4610772" "4919769"		13:36
		"5024735" "5171412" "5429733" "5558568"		
		"5650039" "5692947" "5755859" "5807165"		
		"5833820" "5863412" "5930669" "5933753"		
		"6004880" "6017820").PN.		
-	19	("2751340" "2859166" "3880725" "4148707"	USPAT	2004/02/24
		"4304641" "4420382" "4421627" "4466864"		14:02
		"4678545" "4720329" "4879007" "5084153"		
		"5135636" "5149419" "5230743" "5312532"		
		"5332487" "5582708" "5620581").PN.		
	7	6174425.URPN.	USPAT	2004/02/24
				14:06
-	360	204/222.ccls.	USPAT;	2004/02/24
			US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	817	204/224r.ccls.	USPAT;	2004/02/24
	01,	10 17 11 11 10 10 1	US-PGPUB;	14:12
			EPO; JPO;	• • • •
			DERWENT;	
			IBM_TDB	
	1158	204/222.ccls. 204/224r.ccls.	USPAT;	2004/02/24
_	1136	204/222.0015. 204/2241.0015.	US-PGPUB;	14:13
				14.15
			EPO; JPO;	
			DERWENT;	
	45	(204/222 - 14 204/224 - 15) 1/ 1	IBM_TDB	2004/02/24
_	13	(204/222.ccls. 204/224r.ccls.) and (clean\$3 near	USPAT;	2004/02/24
		(electrode or anode or cathode))	US-PGPUB;	14:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	23	(204/222.ccls. 204/224r.ccls.) and	USPAT;	2004/02/24
		((electropolish\$5) with (electrode or anode or	US-PGPUB;	14:28
		cathode))	EPO; JPO;	
			DERWENT	
-	0	(204/222.ccls. 204/224r.ccls.) and (electrochem\$7	USPAT;	2004/02/24
		near (micromachin\$5 or machin\$5)) and (clean\$ near	US-PGPUB;	14:32
	* [(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	